

RGC80TSX8R

1800V 40A Field Stop Trench IGBT

V _{CES}	1800V
Ι _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	2.2V
P _D	535W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Monolithic Body Diode

with Low Forward Voltage

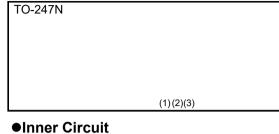
5) Pb - free Lead Plating ; RoHS Compliant

Application

Voltage - resonance Inverter

IH

Outline



(1) Olicetor (1) Olicetor (1) Olicetor (3) Emitter (3) Emitter

Packaging Specifications

	Packaging	Tube		
	Reel Size (mm)	-		
Tuno	Tape Width (mm)	-		
Туре	Basic Ordering Unit (pcs)	450		
	Packing Code	C11		
	Marking	RGC80TSX8R		

•Absolute Maximum Ratings (at T_c = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	1800	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	Ι _C	80	Α
Collector Current	T _C = 100°C	Ι _C	40	Α
Pulsed Collector Current		I _{CP} *1	120	Α
Diode Forward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	I _F	80	Α
	T _C = 100°C	I _F	40	Α
Diode Pulsed Forward Current		I _{FP} ^{*1}	80	Α
Dewer Dissinction	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	535	W
Power Dissipation	T _C = 100°C	P _D	267	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by $T_{jmax.}$

•Thermal Resistance

Deremeter	Symbol		Linit		
Parameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.28	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.28	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol Conditions		Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	1800	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 1860V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V _{CE} = 5V, I _C = 120.7mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 40A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	2.2 2.9	5.0 -	V

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Symbol		Values			1.1	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	9550	-		
Output Capacitance	C _{oes}	V _{GE} = 0V	-	115	-	pF	
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	102	-		
Total Gate Charge	Q _g	V _{CE} = 600V	-	468	-		
Gate - Emitter Charge	Q _{ge}	I _C = 40A	-	93	-	nC	
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	155	-		
Turn - on Delay Time	t _{d(on)}		-	80	-		
Rise Time	t _r	I _C = 40A, V _{CC} = 600V, V _{GE} = 15V, R _G = 10Ω, T _i = 25°C	-	53	-	ns	
Turn - off Delay Time	t _{d(off)}		-	565	-		
Fall Time	t _f	Inductive Load	-	55	-		
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.85	-	ml	
Turn - off Switching Loss	E _{off}		-	1.60	2.15	mJ	
Turn - on Delay Time	t _{d(on)}		-	68	-		
Rise Time	t _r	$I_{\rm C} = 40$ A, $V_{\rm CC} = 600$ V,	-	52	-		
Turn - off Delay Time	t _{d(off)}	$V_{GE} = 15V, R_G = 10\Omega,$ $T_j = 175^{\circ}C$ Inductive Load $*E_{on}$ include diode reverse recovery	-	670	-	ns	
Fall Time	t _f		-	55	-		
Turn - on Switching Loss	E _{on}		-	1.95	-	ml	
Turn - off Switching Loss	E _{off}		-	2.00	-	mJ	

•FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol Conditions —	Values			Unit	
		Min.	Тур.	Max.		
		I _F = 40A, V _{GE} = 0V				
Diode Forward Voltage	V _F	T _j = 25°C	-	1.8	2.3	V
		T _j = 175°C	-	2.4	-	



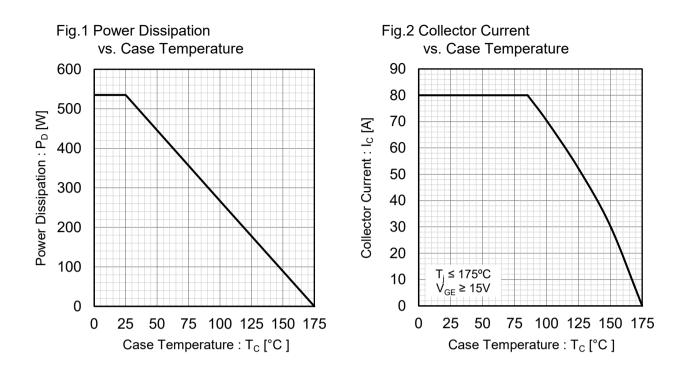
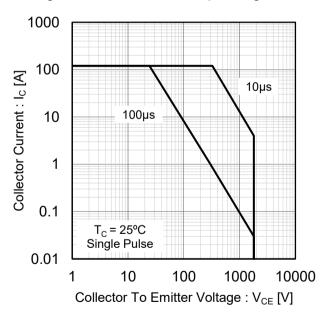
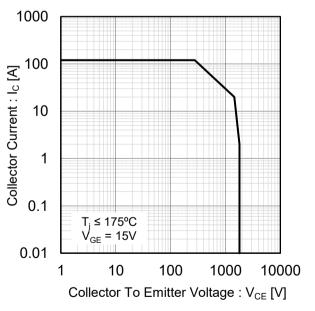


Fig.3 Forward Bias Safe Operating Area







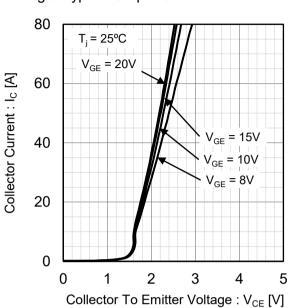


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics

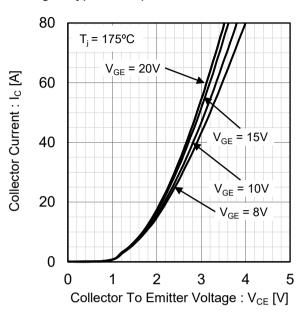
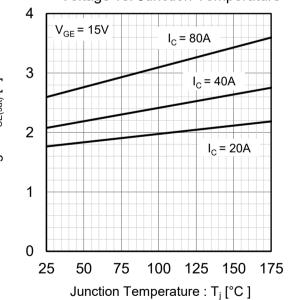
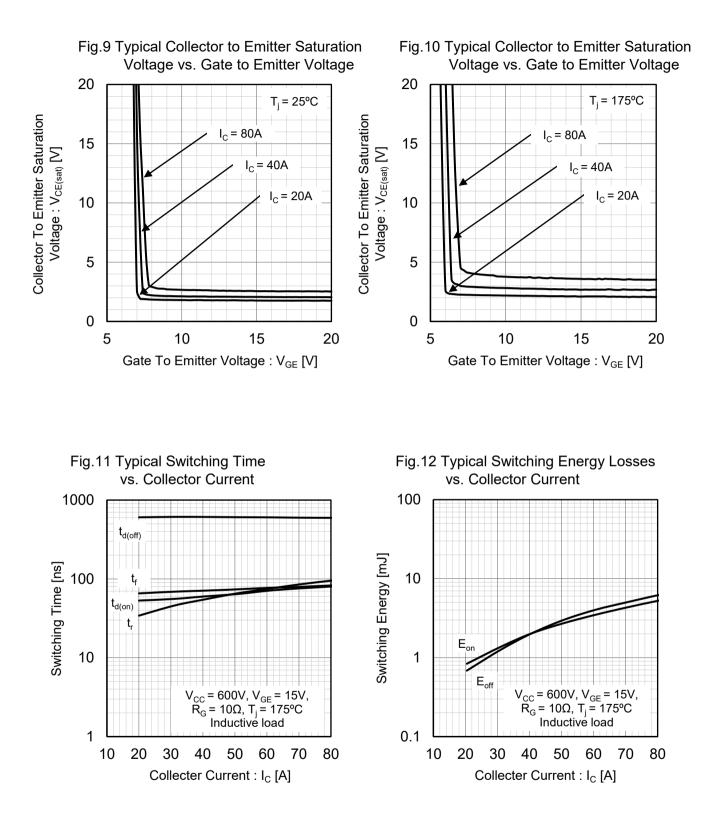


Fig.7 Typical Transfer Characteristics 80 V_{CE} = 10V Collector To Emitter Saturation Collector Current : I_c [A] 60 Voltage : V_{CE(sat)} [V] T_i = 175⁰C 40 T_i = 25°C 20 0 2 0 4 6 8 10 12 Gate To Emitter Voltage : V_{GE} [V]

Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature

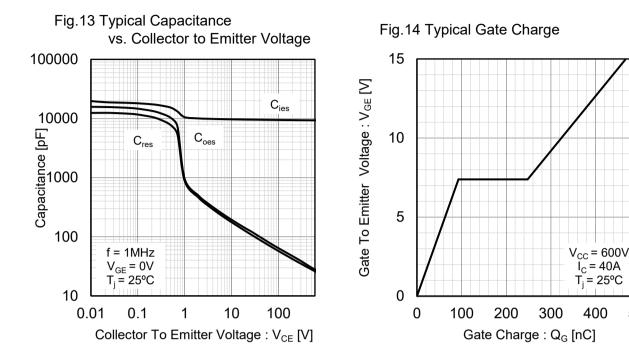


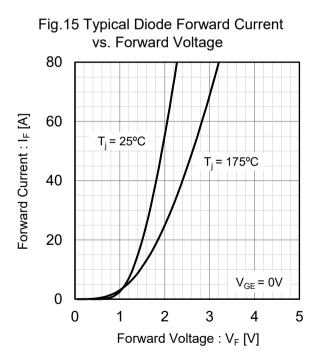


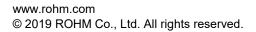
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•Electrical Characteristic Curves







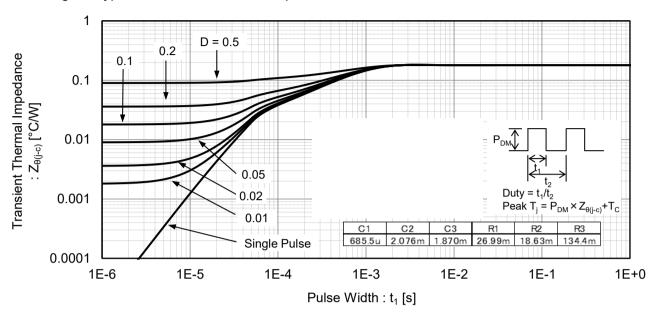


Fig.16 Typical Transient Thermal Impedance

Inductive Load Switching Circuit and Waveform

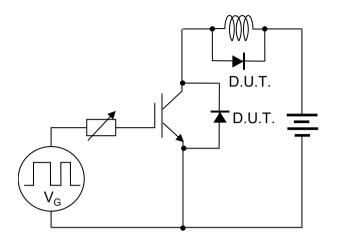


Fig.17 Inductive Load Circuit

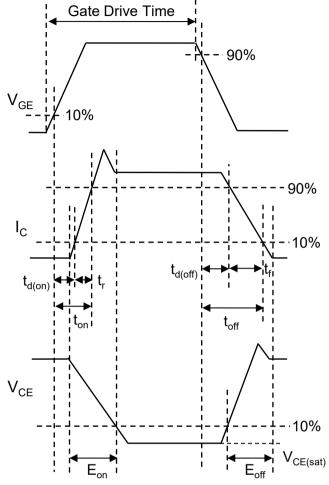


Fig.18 Inductive Load Waveform



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